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# 2N4400

# **MMBT4400**





# **NPN General Purpose Amplifier**

This device is designed for use as general purpose amplifiers and switches requiring collector currents to 500 mA.

### **Absolute Maximum Ratings\***

TA = 25°C unless otherwise noted

| Symbol                            | Parameter  | Value       | Units |
|-----------------------------------|--|-------------|-------|
| $V_{CEO}$                         | Collector-Emitter Voltage                        | 40          | V     |
| V <sub>CBO</sub>                  | Collector-Base Voltage                           | 60          | V     |
| V <sub>EBO</sub>                  | Emitter-Base Voltage                             | 6.0         | V     |
| I <sub>C</sub>                    | Collector Current - Continuous                   | 600         | mA    |
| T <sub>J</sub> , T <sub>stg</sub> | Operating and Storage Junction Temperature Range | -55 to +150 | °C    |

<sup>\*</sup>These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

1) These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

### **Thermal Characteristics**

TA = 25°C unless otherwise noted

| Symbol          | Characteristic Max                         |            | Units      |             |
|-----------------|--|------------|------------|-------------|
|                 |  | 2N4400     | *MMBT4400  |             |
| $P_D$           | Total Device Dissipation Derate above 25°C | 625<br>5.0 | 350<br>2.8 | mW<br>mW/∘C |
| $R_{\theta JC}$ | Thermal Resistance, Junction to Case       | 83.3       |            | °C/W        |
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient    | 200        | 357        | °C/W        |

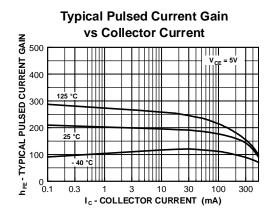
# NPN General Purpose Amplifier (continued)

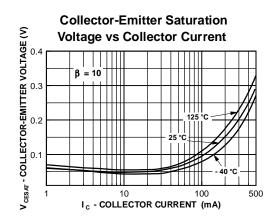
| Symbol  | Parameter  | Test Conditions   | Min              | Max                                  | Units   |
|---|--|---|------------------|--------------------------------------|---|
|   |  |   |                  |                                      |   |
| OFF CHA   | RACTERISTICS   |   |                  |                                      |   |
| V <sub>(BR)CEO</sub>  | Collector-Emitter Breakdown Voltage*   | $I_C = 1.0 \text{ mA}, I_B = 0$   | 40               |                                      | V   |
| V <sub>(BR)CBO</sub>  | Collector-Base Breakdown Voltage   | $I_C = 100  \mu A, I_E = 0$   | 60               |                                      | V   |
| V <sub>(BR)EBO</sub>  | Emitter-Base Breakdown Voltage   | $I_E = 100  \mu A, I_C = 0$   | 6.0              |                                      | V   |
| I <sub>CEX</sub>  | Collector Cutoff Current   | V <sub>CE</sub> = 35 V, V <sub>EB</sub> = 0.4 V   |                  | 0.1                                  | μΑ  |
| I <sub>BL</sub>   | Emitter Cutoff Current   | $V_{CE} = 35 \text{ V}, \ V_{EB} = 0.4 \text{ V}$   |                  | 0.1                                  | μΑ  |
|   |  |   |                  |                                      |   |
| ON CHAF   | RACTERISTICS*  |   |                  |                                      |   |
| h <sub>FE</sub>   | DC Current Gain  | $V_{CE} = 1.0 \text{ V}, I_{C} = 1.0 \text{ mA}$  | 20               |                                      |   |
|   |  | $V_{CE} = 1.0 \text{ V}, I_{C} = 10 \text{ mA}$   | 40               |                                      |   |
|   |  | $V_{CE} = 1.0 \text{ V}, I_{C} = 150 \text{ mA}$  | 50               | 150                                  |   |
| \/  | Collector-Emitter Saturation Voltage   | $V_{CE} = 2.0 \text{ V}, I_{C} = 500 \text{ mA}$<br>$I_{C} = 150 \text{ mA}, I_{B} = 15 \text{ mA}$   | 20               | 0.40                                 | V   |
| $V_{CE(sat)}$   | Collector-Emitter Saturation Voltage   | $I_C = 150 \text{ mA}, I_B = 15 \text{ mA}$<br>$I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$  |                  | 0.40                                 | V V   |
| V <sub>BE(sat)</sub>  | Base-Emitter Saturation Voltage  | I <sub>C</sub> = 150 mA, I <sub>B</sub> = 15 mA   | 0.75             | 0.95                                 | V   |
| · DE(Sat)   |  | , 5   |                  |                                      |   |
|   |  | $I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$   |                  | 1.2                                  | V   |
| SMALL S   | IGNAL CHARACTERISTICS  |   |                  |                                      |   |
|   | Output Capacitance   | V <sub>CB</sub> = 5.0 V, f = 140 kHz  |                  | 6.5                                  | pF  |
| C <sub>ob</sub>   | Output Capacitance Input Capacitance   | $V_{CB} = 5.0 \text{ V}, f = 140 \text{ kHz}$<br>$V_{EB} = 0.5 \text{ V}, f = 140 \text{ kHz}$  |                  |                                      |   |
| C <sub>ob</sub>   | Output Capacitance   | $V_{CB} = 5.0 \text{ V}, f = 140 \text{ kHz}$ $V_{EB} = 0.5 \text{ V}, f = 140 \text{ kHz}$ $I_{C} = 20 \text{ mA}, V_{CE} = 10 \text{ V},$ $f = 100 \text{ MHz}$   | 2.0              | 6.5                                  | pF  |
| C <sub>ob</sub><br>C <sub>ib</sub>  | Output Capacitance Input Capacitance   | $V_{CB} = 5.0 \text{ V}, f = 140 \text{ kHz}$ $V_{EB} = 0.5 \text{ V}, f = 140 \text{ kHz}$ $I_{C} = 20 \text{ mA}, V_{CE} = 10 \text{ V},$   | 2.0              | 6.5                                  | pF  |
| C <sub>ob</sub> C <sub>ib</sub> h <sub>fe</sub>   | Output Capacitance Input Capacitance Small-Signal Current Gain   | $V_{CB} = 5.0 \text{ V}, f = 140 \text{ kHz}$ $V_{EB} = 0.5 \text{ V}, f = 140 \text{ kHz}$ $I_{C} = 20 \text{ mA}, V_{CE} = 10 \text{ V},$ $f = 100 \text{ MHz}$   | _                | 6.5                                  | pF  |
| SMALL S Cob Cib hfe hfe hre   | Output Capacitance Input Capacitance Small-Signal Current Gain Small-Signal Current Gain   | $V_{CB} = 5.0 \text{ V, } f = 140 \text{ kHz}$ $V_{EB} = 0.5 \text{ V, } f = 140 \text{ kHz}$ $I_{C} = 20 \text{ mA, } V_{CE} = 10 \text{ V, }$ $f = 100 \text{ MHz}$ $V_{CE} = 10 \text{ V, } I_{C} = 1.0 \text{ mA, }$  | 20               | 6.5 30 250                           | pF<br>pF                                      |
| Cob<br>Cib<br>hfe<br>hfe<br>hie<br>hre  | Output Capacitance Input Capacitance Small-Signal Current Gain Small-Signal Current Gain Input Impedance   | $V_{CB} = 5.0 \text{ V, } f = 140 \text{ kHz}$ $V_{EB} = 0.5 \text{ V, } f = 140 \text{ kHz}$ $I_{C} = 20 \text{ mA, } V_{CE} = 10 \text{ V, }$ $f = 100 \text{ MHz}$ $V_{CE} = 10 \text{ V, } I_{C} = 1.0 \text{ mA, }$  | 20               | 6.5<br>30<br>250<br>7.5              | pF<br>pF                                      |
| C <sub>ob</sub> C <sub>ib</sub> h <sub>fe</sub> h <sub>ie</sub>   | Output Capacitance Input Capacitance Small-Signal Current Gain Small-Signal Current Gain Input Impedance Voltage Feedback Ratio  | $V_{CB} = 5.0 \text{ V, } f = 140 \text{ kHz}$ $V_{EB} = 0.5 \text{ V, } f = 140 \text{ kHz}$ $I_{C} = 20 \text{ mA, } V_{CE} = 10 \text{ V, }$ $f = 100 \text{ MHz}$ $V_{CE} = 10 \text{ V, } I_{C} = 1.0 \text{ mA, }$  | 20<br>0.5<br>0.1 | 6.5<br>30<br>250<br>7.5<br>8.0       | pF<br>pF<br>ΚΩ<br>x 10 <sup>-4</sup>          |
| Cob Cib hfe hfe hie hre   | Output Capacitance Input Capacitance Small-Signal Current Gain Small-Signal Current Gain Input Impedance Voltage Feedback Ratio  | $V_{CB} = 5.0 \text{ V, } f = 140 \text{ kHz}$ $V_{EB} = 0.5 \text{ V, } f = 140 \text{ kHz}$ $I_{C} = 20 \text{ mA, } V_{CE} = 10 \text{ V, }$ $f = 100 \text{ MHz}$ $V_{CE} = 10 \text{ V, } I_{C} = 1.0 \text{ mA, }$  | 20<br>0.5<br>0.1 | 6.5<br>30<br>250<br>7.5<br>8.0       | pF<br>pF<br>ΚΩ<br>x 10 <sup>-4</sup>          |
| Cob Cib hfe hfe hie hre   | Output Capacitance Input Capacitance Small-Signal Current Gain Small-Signal Current Gain Input Impedance Voltage Feedback Ratio Output Admittance                                | $V_{CB} = 5.0 \text{ V, } f = 140 \text{ kHz}$ $V_{EB} = 0.5 \text{ V, } f = 140 \text{ kHz}$ $I_{C} = 20 \text{ mA, } V_{CE} = 10 \text{ V, }$ $f = 100 \text{ MHz}$ $V_{CE} = 10 \text{ V, } I_{C} = 1.0 \text{ mA, }$  | 20<br>0.5<br>0.1 | 6.5<br>30<br>250<br>7.5<br>8.0       | pF<br>pF<br>ΚΩ<br>x 10 <sup>-4</sup>          |
| C <sub>ob</sub> C <sub>ib</sub> h <sub>fe</sub> h <sub>fe</sub> h <sub>ie</sub> h <sub>re</sub> h <sub>oe</sub> | Output Capacitance Input Capacitance Small-Signal Current Gain Small-Signal Current Gain Input Impedance Voltage Feedback Ratio Output Admittance  NG CHARACTERISTICS            | $V_{CB} = 5.0 \text{ V}, f = 140 \text{ kHz}$ $V_{EB} = 0.5 \text{ V}, f = 140 \text{ kHz}$ $I_{C} = 20 \text{ mA}, V_{CE} = 10 \text{ V},$ $f = 100 \text{ MHz}$ $V_{CE} = 10 \text{ V}, I_{C} = 1.0 \text{ mA},$ $f = 1.0 \text{ kHz}$  | 20<br>0.5<br>0.1 | 6.5<br>30<br>250<br>7.5<br>8.0<br>30 | pF<br>pF<br>KΩ<br>x 10 <sup>-4</sup><br>μmhos |
| Cob Cib hfe hfe hie hoe   | Output Capacitance Input Capacitance Small-Signal Current Gain Small-Signal Current Gain Input Impedance Voltage Feedback Ratio Output Admittance  NG CHARACTERISTICS Delay Time | $V_{CB} = 5.0 \text{ V}, f = 140 \text{ kHz}$ $V_{EB} = 0.5 \text{ V}, f = 140 \text{ kHz}$ $I_{C} = 20 \text{ mA}, V_{CE} = 10 \text{ V},$ $f = 100 \text{ MHz}$ $V_{CE} = 10 \text{ V}, I_{C} = 1.0 \text{ mA},$ $f = 1.0 \text{ kHz}$ $V_{CC} = 30 \text{ V}, I_{C} = 150 \text{ mA},$ | 20<br>0.5<br>0.1 | 6.5<br>30<br>250<br>7.5<br>8.0<br>30 | pF<br>pF<br>KΩ<br>x 10 <sup>-4</sup><br>μmhos |

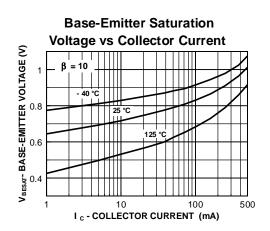
<sup>\*</sup>Pulse Test: Pulse Width £ 300 ms, Duty Cycle £ 2.0%

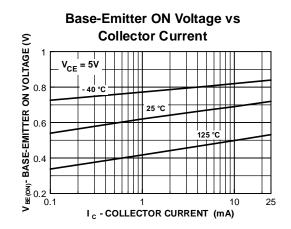
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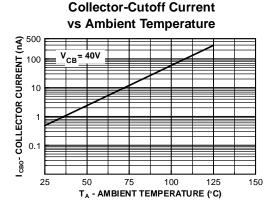
### **Typical Characteristics**

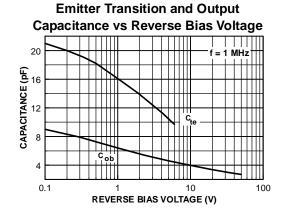








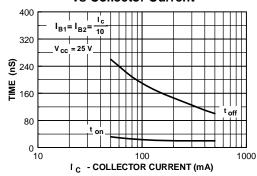




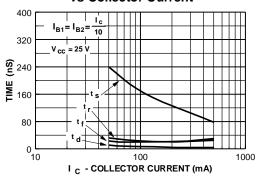
(continued)

### Typical Characteristics (continued)

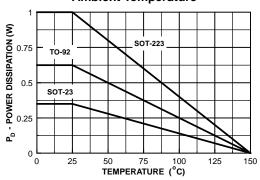
Turn On and Turn Off Times vs Collector Current



# Switching Times vs Collector Current

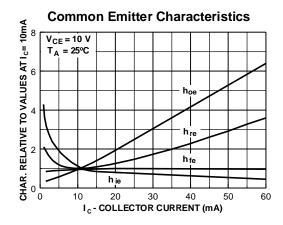


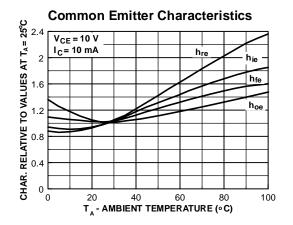
Power Dissipation vs Ambient Temperature

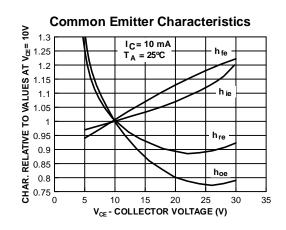


(continued)

# **Typical Common Emitter Characteristics** (f = 1.0kHz)







(continued)

# **Test Circuits**

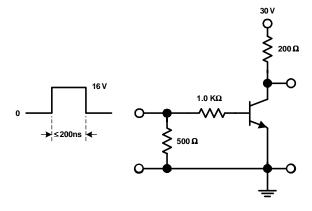


FIGURE 1: Saturated Turn-On Switching Timer

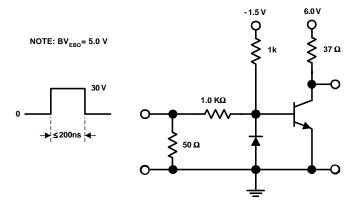


FIGURE 2: Saturated Turn-Off Switching Time

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